

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-9 have been withdrawn from consideration.

10. (Amended) A high voltage semiconductor device comprising:
a semiconductor substrate, the semiconductor substrate including a plurality of device structures thereon; and
an interconnect on the semiconductor substrate, the interconnect comprising at least one slot provided in the semiconductor substrate and at least one metal within the slot, the at least one metal being of sufficient thickness to carry a high current, wherein the at least one slot is oxidized everywhere except at the bottom of the slot where the interconnect forms a ground.

11. (original) The semiconductor device of claim 10 wherein the metal comprises a plurality of metals.

12. (original) The semiconductor device of claim 11 wherein the plurality of metals comprises two metals, a first metal covers one-half of the slot and a second metal fills the slot.

13. (original) The semiconductor device of claim 12 wherein the plurality of metals comprises three metals, wherein the first and second metals fill the slot and the third metal provides an interconnect layer.

14. (original) The semiconductor device of claim 13 wherein the ground strap comprises an ideal short to ground.

15. (original) The semiconductor device of claim 14 wherein the ground strap provides for isolation between components.

16. (amended) A high voltage interconnect on a semiconductor substrate comprising:

at least one slot provided in the semiconductor substrate; and

at least one metal within the slot, the at least one metal being of sufficient thickness to carry a high current, wherein the at least one slot is oxidized everywhere except at the bottom of the slot, and the interconnect forms a very low resistance ground strap.

17. (original) The interconnect of claim 16 wherein the metal comprises a plurality of metals.

18. (original) The interconnect of claim 17 wherein the plurality of metals comprises two metals, a first metal covers one-half of the slot and a second metal fills the slot.

19. (original) The interconnect of claim 16 wherein the plurality of metals comprises three metals, wherein the first and second metals fill the slot and the third metal provides an interconnect layer.

20. (original) The interconnect of claim 16 wherein the ground strap comprises an ideal short to ground.

21. (original) The interconnect of claim 16 wherein the ground strap provides for isolation between components.